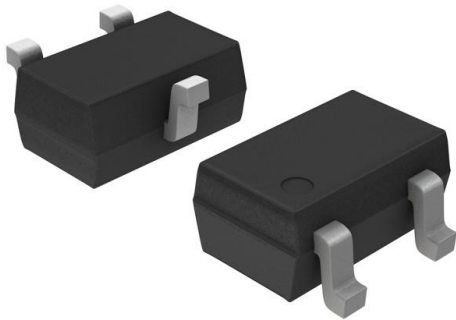


MUN5131T1G Datasheet

www.digi-electronics.com



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	MUN5131T1G-DG
Manufacturer	onsemi
Manufacturer Product Number	MUN5131T1G
Description	TRANS PREBIAS PNP 50V SC70-3
Detailed Description	Pre-Biased Bipolar Transistor (BJT) PNP - Pre-Biased 50 V 100 mA 202 mW Surface Mount SC-70-3 (SOT323)



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.

Purchase and inquiry

Manufacturer Product Number:

MUN5131T1G

Series:

-

Transistor Type:

PNP - Pre-Biased

Voltage - Collector Emitter Breakdown (Max):

50 V

Resistor - Emitter Base (R2):

2.2 kOhms

Vce Saturation (Max) @ Ib, Ic:

250mV @ 5mA, 10mA

Power - Max:

202 mW

Package / Case:

SC-70, SOT-323

Base Product Number:

MUN5131

Manufacturer:

onsemi

Product Status:

Active

Current - Collector (Ic) (Max):

100 mA

Resistor - Base (R1):

2.2 kOhms

DC Current Gain (hFE) (Min) @ Ic, Vce:

8 @ 5mA, 10V

Current - Collector Cutoff (Max):

500nA

Mounting Type:

Surface Mount

Supplier Device Package:

SC-70-3 (SOT323)

Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.21.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

Digital Transistors (BRT)

R1 = 2.2 kΩ, R2 = 2.2 kΩ

PNP Transistors with Monolithic Bias Resistor Network

MUN2131, MMUN2131L, MUN5131, DTA123EE, DTA123EM3, NSBA123EF3

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

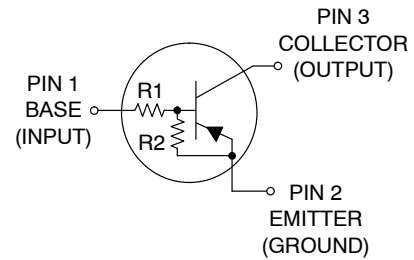
- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25°C)

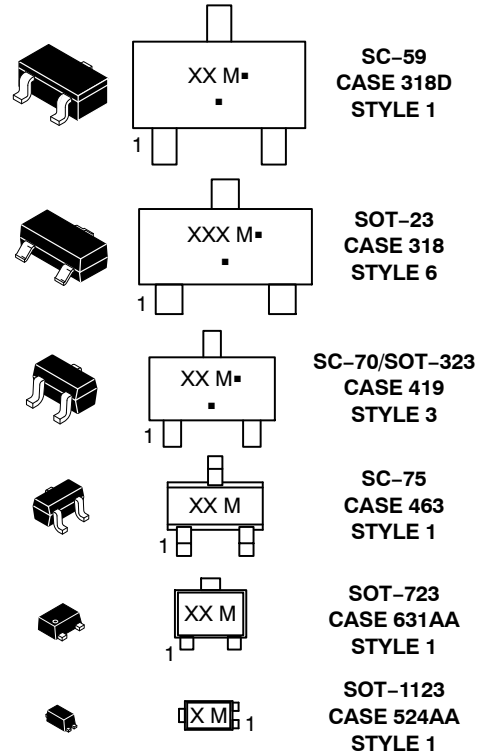
Rating	Symbol	Max	Unit
Collector-Base Voltage	V _{CBO}	50	Vdc
Collector-Emitter Voltage	V _{CEO}	50	Vdc
Collector Current - Continuous	I _C	100	mAdc
Input Forward Voltage	V _{IN(fwd)}	12	Vdc
Input Reverse Voltage	V _{IN(rev)}	10	Vdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

PIN CONNECTIONS



MARKING DIAGRAMS



XXX = Specific Device Code
 M = Date Code*
 ■ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

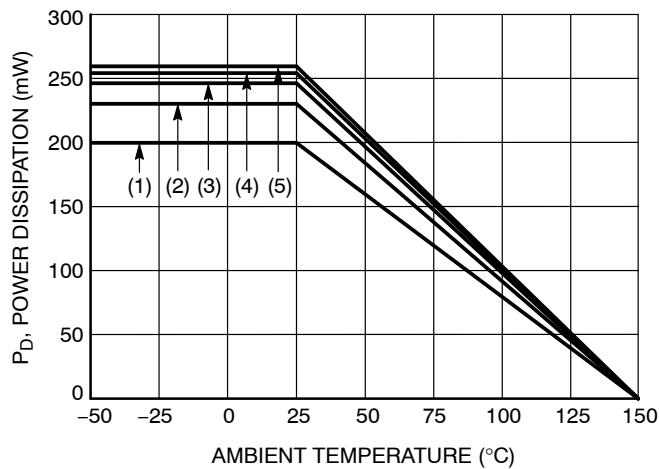
See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

MUN2131, MMUN2131L, MUN5131, DTA123EE, DTA123EM3, NSBA123EF3**Table 1. ORDERING INFORMATION**

Device	Part Marking	Package	Shipping [†]
MUN2131T1G	6H	SC-59 (Pb-Free)	3000 / Tape & Reel
MMUN2131LT1G, NSVMUN2131LT1G*	A6H	SOT-23 (Pb-Free)	3000 / Tape & Reel
MUN5131T1G, NSVMUN5131T1G*	6H	SC-70/SOT-323 (Pb-Free)	3000 / Tape & Reel
DTA123EET1G	6H	SC-75 (Pb-Free)	3000 / Tape & Reel
DTA123EM3T5G, NSVDTA123EM3T5G*	6H	SOT-723 (Pb-Free)	8000 / Tape & Reel
NSBA123EF3T5G	P (180°)**	SOT-1123 (Pb-Free)	8000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

** (xx°) = Degree rotation in the clockwise direction.



- (1) SC-75 and SC-70/SOT323; Minimum Pad
- (2) SC-59; Minimum Pad
- (3) SOT-23; Minimum Pad
- (4) SOT-1123; 100 mm², 1 oz. copper trace
- (5) SOT-723; Minimum Pad

Figure 1. Derating Curve

MUN2131, MMUN2131L, MUN5131, DTA123EE, DTA123EM3, NSBA123EF3**Table 2. THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
THERMAL CHARACTERISTICS (SC-59) (MUN2131)			
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	P_D 230 338 1.8 2.7	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{\theta JA}$ 540 370	$^\circ\text{C/W}$
Thermal Characterization Parameter, Junction to Lead Thermal Characterization Parameter, Junction to Top	Ψ_{JL} Ψ_{JT}	264 287	$^\circ\text{C/W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$
THERMAL CHARACTERISTICS (SOT-23) (MMUN2131L)			
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	P_D 246 400 2.0 3.2	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{\theta JA}$ 508 311	$^\circ\text{C/W}$
Thermal Characterization Parameter, Junction to Lead Thermal Characterization Parameter, Junction to Top	Ψ_{JL} Ψ_{JT}	174 208	$^\circ\text{C/W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$
THERMAL CHARACTERISTICS (SC-70/SOT-323) (MUN5131)			
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	P_D 202 310 1.6 2.5	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{\theta JA}$ 618 403	$^\circ\text{C/W}$
Thermal Characterization Parameter, Junction to Lead Thermal Characterization Parameter, Junction to Top	Ψ_{JL} Ψ_{JT}	280 332	$^\circ\text{C/W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$
THERMAL CHARACTERISTICS (SC-75) (DTA123EE)			
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	P_D 200 300 1.6 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{\theta JA}$ 600 400	$^\circ\text{C/W}$
Thermal Characterization Parameter, Junction to Lead Thermal Characterization Parameter, Junction to Top	Ψ_{JL} Ψ_{JT}	277 245	$^\circ\text{C/W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$
THERMAL CHARACTERISTICS (SOT-723) (DTA123EM3)			
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	P_D 260 600 2.0 4.8	mW mW/ $^\circ\text{C}$

- FR-4 @ Minimum Pad.
- FR-4 @ 1.0 x 1.0 Inch Pad.
- FR-4 @ 100 mm², 1 oz. copper traces, still air.
- FR-4 @ 500 mm², 1 oz. copper traces, still air.

MUN2131, MMUN2131L, MUN5131, DTA123EE, DTA123EM3, NSBA123EF3**Table 2. THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
THERMAL CHARACTERISTICS (SOT-723) (DTA123EM3)			
Thermal Resistance, Junction to Ambient (Note 1) (Note 2)	$R_{\theta JA}$	480 205	$^{\circ}\text{C}/\text{W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^{\circ}\text{C}$
THERMAL CHARACTERISTICS (SOT-1123) (NSBA123EF3)			
Total Device Dissipation $T_A = 25^{\circ}\text{C}$ (Note 3) Derate above 25°C (Note 4)	P_D	254 297 2.0 2.4	mW mW/ $^{\circ}\text{C}$
Thermal Resistance, Junction to Ambient (Note 3) (Note 4)	$R_{\theta JA}$	493 421	$^{\circ}\text{C}/\text{W}$
Thermal Characterization Parameter, Junction to Lead Thermal Characterization Parameter, Junction to Top	Ψ_{JL} Ψ_{JT}	110 85	$^{\circ}\text{C}/\text{W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^{\circ}\text{C}$

- FR-4 @ Minimum Pad.
- FR-4 @ 1.0 x 1.0 Inch Pad.
- FR-4 @ 100 mm², 1 oz. copper traces, still air.
- FR-4 @ 500 mm², 1 oz. copper traces, still air.

Table 3. ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}\text{C}$, unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Base Cutoff Current ($V_{CB} = 50\text{ V}, I_E = 0$)	I_{CBO}	-	-	100	nAdc
Collector-Emitter Cutoff Current ($V_{CE} = 50\text{ V}, I_B = 0$)	I_{CEO}	-	-	500	nAdc
Emitter-Base Cutoff Current ($V_{EB} = 6.0\text{ V}, I_C = 0$)	I_{EBO}	-	-	2.3	mAdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu\text{A}, I_E = 0$)	$V_{(BR)CBO}$	50	-	-	Vdc
Collector-Emitter Breakdown Voltage (Note 5) ($I_C = 2.0\text{ mA}, I_B = 0$)	$V_{(BR)CEO}$	50	-	-	Vdc
ON CHARACTERISTICS					
DC Current Gain (Note 5) ($I_C = 5.0\text{ mA}, V_{CE} = 10\text{ V}$)	h_{FE}	8.0	15	-	
Collector-Emitter Saturation Voltage (Note 5) ($I_C = 10\text{ mA}, I_B = 5.0\text{ mA}$)	$V_{CE(sat)}$	-	-	0.25	Vdc
Input Voltage (off) ($V_{CE} = 5.0\text{ V}, I_C = 100\ \mu\text{A}$)	$V_{i(off)}$	-	1.2	0.5	Vdc
Input Voltage (on) ($V_{CE} = 0.3\text{ V}, I_C = 20\text{ mA}$)	$V_{i(on)}$	2.0	1.7	-	Vdc
Output Voltage (on) ($V_{CC} = 5.0\text{ V}, V_B = 2.5\text{ V}, R_L = 1.0\text{ k}\Omega$)	V_{OL}	-	-	0.2	Vdc
Output Voltage (off) ($V_{CC} = 5.0\text{ V}, V_B = 0.25\text{ V}, R_L = 1.0\text{ k}\Omega$)	V_{OH}	4.9	-	-	Vdc
Input Resistor	R_1	1.5	2.2	2.9	k Ω
Resistor Ratio	R_1/R_2	0.8	1.0	1.2	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- Pulsed Condition: Pulse Width = 300 msec, Duty Cycle $\leq 2\%$.

MUN2131, MMUN2131L, MUN5131, DTA123EE, DTA123EM3, NSBA123EF3

**TYPICAL CHARACTERISTICS
MUN2131, MMUN2131L, MUN5131, DTA123EE, DTA123EM3**

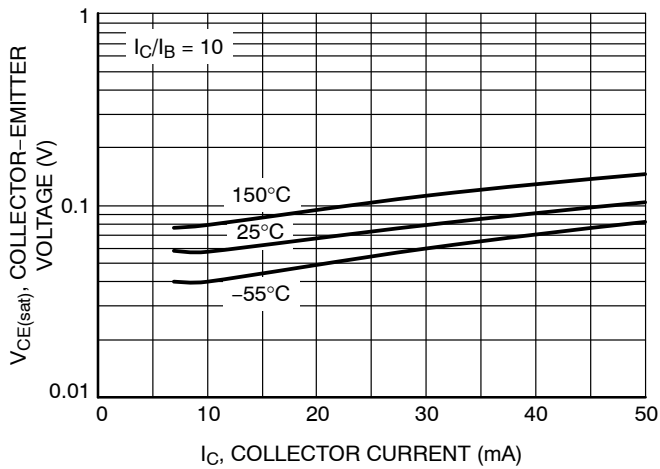


Figure 2. $V_{CE(sat)}$ vs. I_C

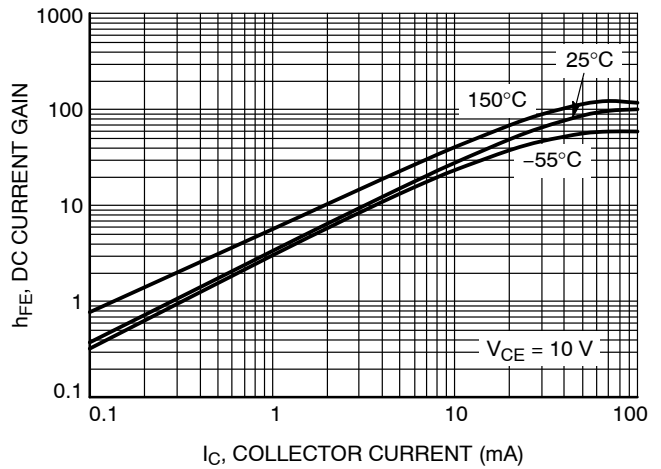


Figure 3. DC Current Gain

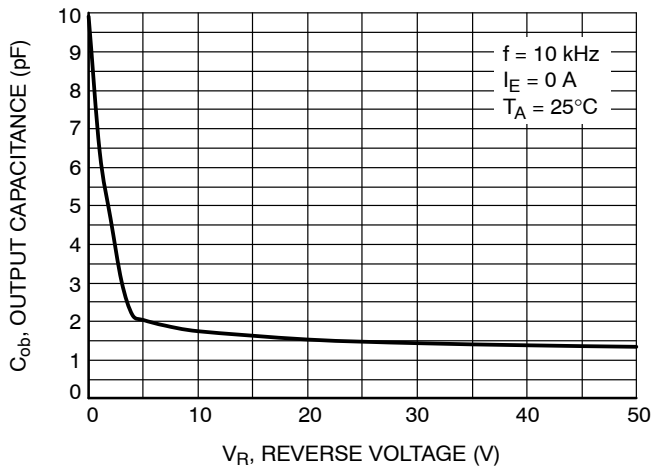


Figure 4. Output Capacitance

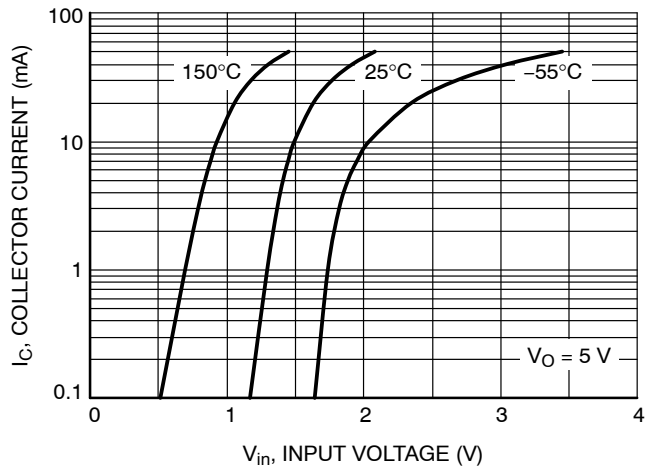


Figure 5. Output Current vs. Input Voltage

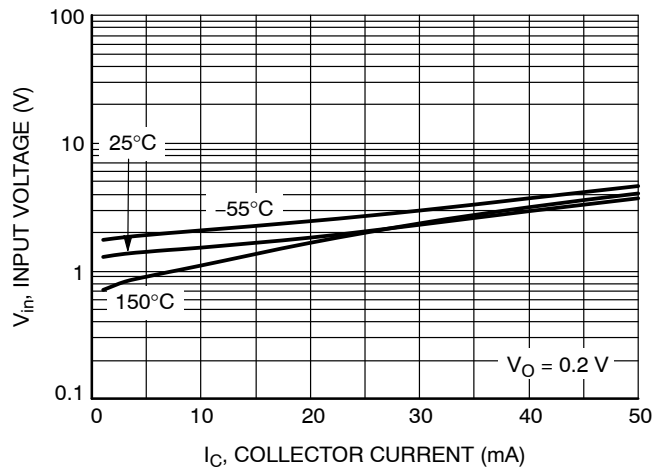
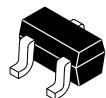


Figure 6. Input Voltage vs. Output Current



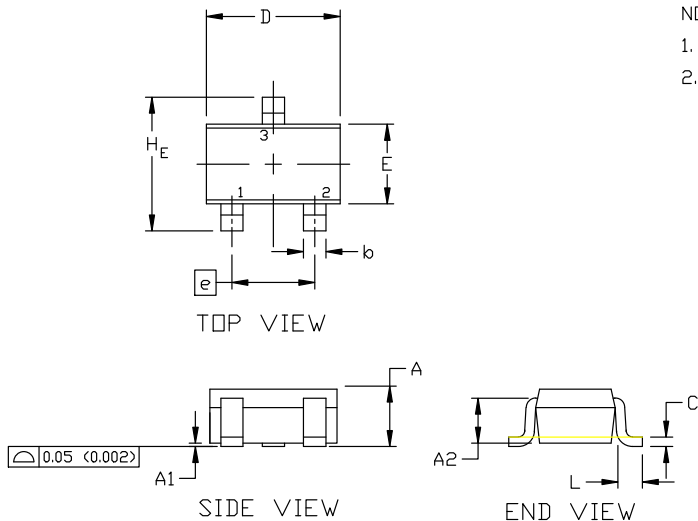
**MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS**



SCALE 4:1

**SC-70 (SOT-323)
CASE 419
ISSUE R**

DATE 11 OCT 2022

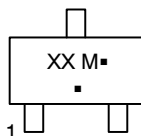


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH

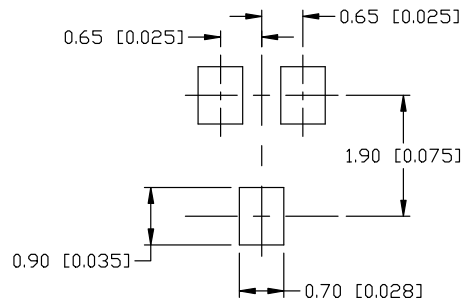
DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
H _E	2.00	2.10	2.40	0.079	0.083	0.095

**GENERIC
MARKING DIAGRAM**



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

SOLDERING FOOTPRINT

- STYLE 1:
CANCELLED
- STYLE 2:
PIN 1. ANODE
2. N.C.
3. CATHODE
- STYLE 3:
PIN 1. BASE
2. EMITTER
3. COLLECTOR
- STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE
- STYLE 5:
PIN 1. ANODE
2. ANODE
3. CATHODE
- STYLE 6:
PIN 1. EMITTER
2. BASE
3. COLLECTOR
- STYLE 7:
PIN 1. BASE
2. EMITTER
3. COLLECTOR
- STYLE 8:
PIN 1. GATE
2. SOURCE
3. DRAIN
- STYLE 9:
PIN 1. ANODE
2. CATHODE
3. CATHODE-ANODE
- STYLE 10:
PIN 1. CATHODE
2. ANODE
3. ANODE-CATHODE
- STYLE 11:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

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DESCRIPTION:	SC-70 (SOT-323)	PAGE 1 OF 1

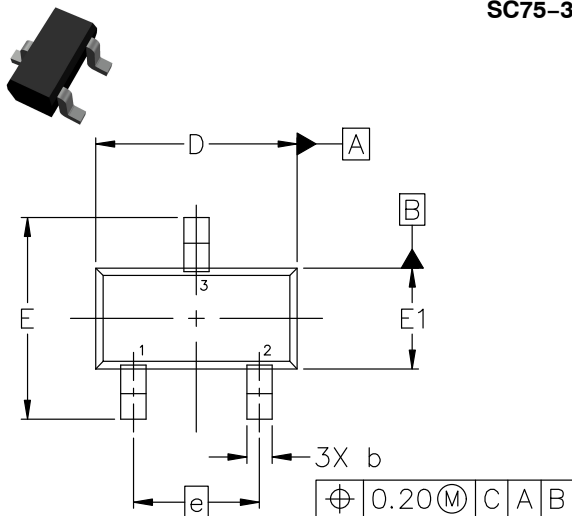
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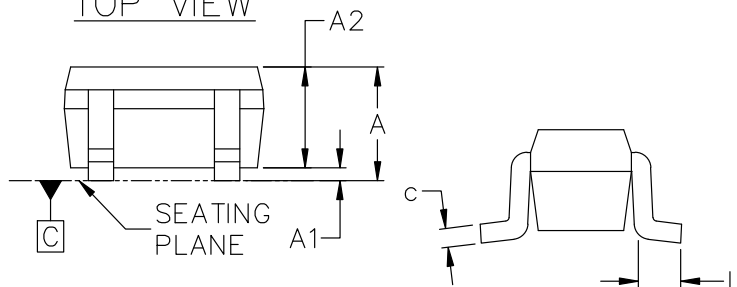
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

SC75-3 1.60x0.80x0.80, 1.00P
CASE 463
ISSUE H

DATE 01 FEB 2024



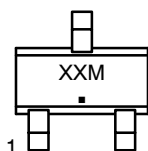
TOP VIEW



SIDE VIEW

END VIEW

GENERIC MARKING DIAGRAM*



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Package

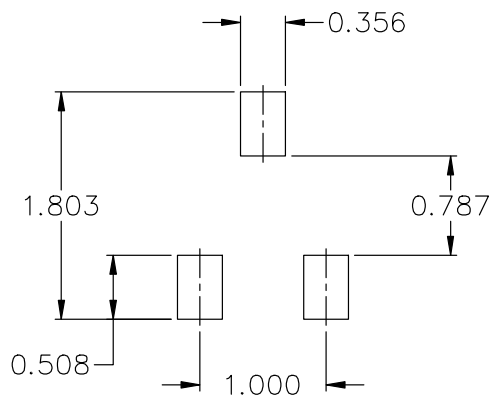
*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

- STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR
- STYLE 2:
PIN 1. ANODE
2. N/C
3. CATHODE
- STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE
- STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE
- STYLE 5:
PIN 1. GATE
2. SOURCE
3. DRAIN

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
2. ALL DIMENSION ARE IN MILLIMETERS.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.70	0.80	0.90
A1	0.00	0.05	0.10
A2	0.80 REF.		
b	0.15	0.20	0.30
c	0.10	0.15	0.25
D	1.55	1.60	1.65
E	1.50	1.60	1.70
E1	0.70	0.80	0.90
e	1.00 BSC		
L	0.10	0.15	0.20



RECOMMENDED MOUNTING FOOTPRINT*

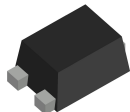
* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

DOCUMENT NUMBER:	98ASB15184C	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SC75-3 1.60x0.80x0.80, 1.00P	PAGE 1 OF 1

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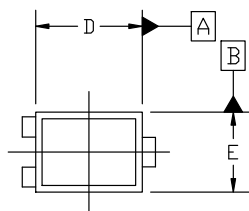


**MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS**

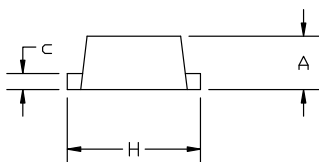


**SOT-1123 0.80x0.60x0.37, 0.35P
CASE 524AA
ISSUE D**

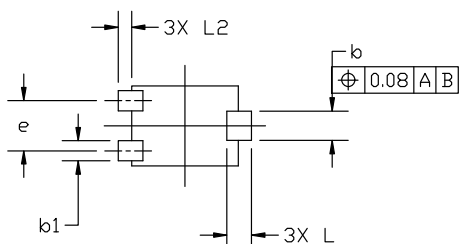
DATE 18 JAN 2024



TOP VIEW

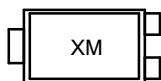


SIDE VIEW



BOTTOM VIEW

GENERIC MARKING DIAGRAM*



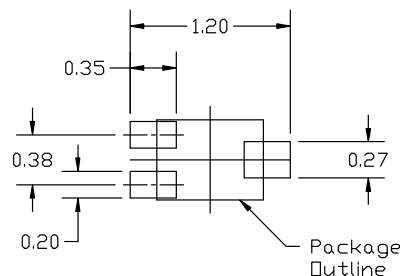
X = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.34	0.37	0.40
b	0.15	0.22	0.28
b1	0.10	0.15	0.20
c	0.07	0.12	0.17
D	0.75	0.80	0.85
E	0.55	0.60	0.65
e	0.35	0.38	0.40
H	0.950	1.000	1.050
L	0.185 REF		
L2	0.05	0.10	0.15



RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference manual, SOLDERM/D.

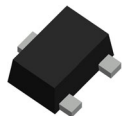
STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE	STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN
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DESCRIPTION:	SOT-1123 0.80x0.60x0.37, 0.35P	PAGE 1 OF 1

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**MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS**



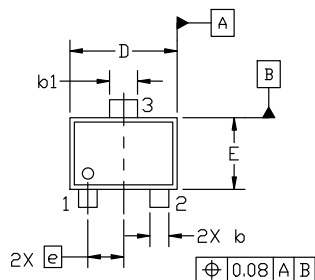
**SOT-723 1.20x0.80x0.50, 0.40P
CASE 631AA
ISSUE E**

DATE 24 JAN 2024

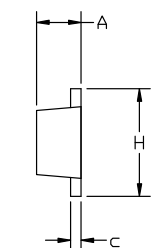
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

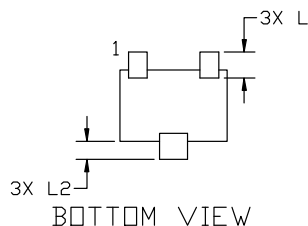
DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
c	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
e	0.40 BSC		
H	1.15	1.20	1.25
L	0.29 REF		
L2	0.15	0.20	0.25



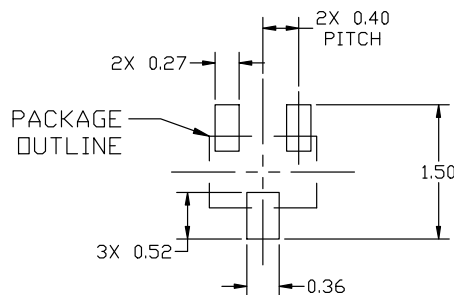
TOP VIEW



SIDE VIEW

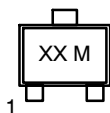


BOTTOM VIEW



RECOMMENDED MOUNTING FOOTPRINT

GENERIC MARKING DIAGRAM*



XX = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. GATE
2. EMITTER	2. N/C	2. ANODE	2. CATHODE	2. SOURCE
3. COLLECTOR	3. CATHODE	3. CATHODE	3. ANODE	3. DRAIN

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